

## 产品概览

### FCP190N65S3R0: Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 17 A, 190 mΩ, TO-220

欲看完整文档，请参阅数据表。

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

#### 特性

- 700 V @ T<sub>J</sub> = 150 °C
- Low Effective Output Capacitance (Typ. C<sub>oss</sub>(eff.) = 300 pF)
- Ultra Low Gate Charge (Typ. Q<sub>g</sub> = 33 nC)
- Optimized Capacitance
- 100% Avalanche Tested
- RoHS Compliant
- Typ. R<sub>DS(on)</sub> = 159 mΩ
- Internal Gate Resistance: 0.5Ω

#### 应用

- Computing
- Consumer
- Industrial

#### 优势

- Higher system reliability at low temperature operation
- Low switching loss
- Low switching loss
- Lower peak V<sub>ds</sub> and lower V<sub>gs</sub> oscillation

#### 终端产品

- Notebook / Desktop computer / Game console
- Telecom / Server
- LCD / LED TV
- LED Lighting / Ballast
- Adapter

#### 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V <sub>DS(BR)</sub> Min (V)	V <sub>GS</sub> Max (V)	V <sub>GS(th)</sub> Max (V)	I <sub>D</sub> Max (A)	P <sub>D</sub> Max (W)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 2.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 4.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 10 V (mΩ)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 4.5 V (nC)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 10 V (nC)	C <sub>iss</sub> Typ (pF)	Package Type
FCP190N65S3R0	0.9534	Pb-free Halide free	Active	N-Channel	Single	650	±30	4.5	17	144	-	-	159	-	33	1350	TO-220-3

欲了解更多信息，请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

创建于：10/22/2019